

Professor



Sihyun Kim

- (2014) **B. S.**, Dep. Electrical and Computer Engineering, **Seoul National University**
- (2022) **Ph. D.**, Dep. Electrical and Computer Engineering, **Seoul National University**

EDUCATION

EXPERIENCE

- (2023. 03 - Current) **Assistant Professor**, Dep. Electronic Engineering, **Sogang University**
- (2022. 09 - 2023. 02) **Staff Engineer**, Semiconductor R&D Center, **Samsung Electronics**
- (2014. 03 - 2022. 08) **Lecturer** (Ion Implantation), ISRC, **Seoul National University**
- (2014. 07 - 2019. 07) **Lecturer** (Nano CMOS Simulation), ISRC, **Seoul National University**

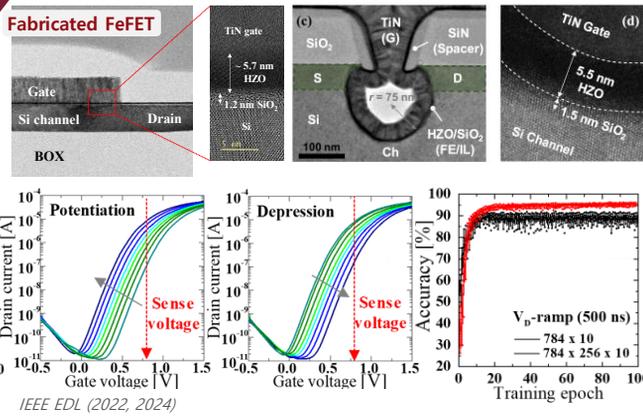
AWARDS

- Samsung HumanTech Paper Awards (Silver Prize), Samsung Electronics (2024)
- Distinguished Dissertation Award, ECE, Seoul National University (2022)
- Outstanding Paper Award, SNU-Samsung R&DB Center (2021)
- Outstanding Student Paper Award, IEIE (2018)

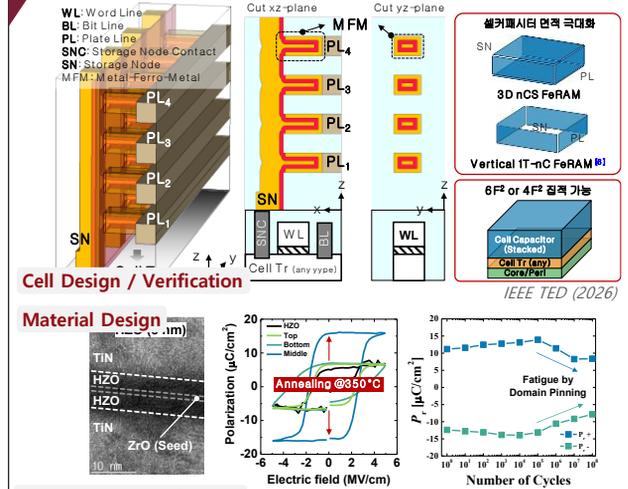
Research Topics

Ferroelectric Memories

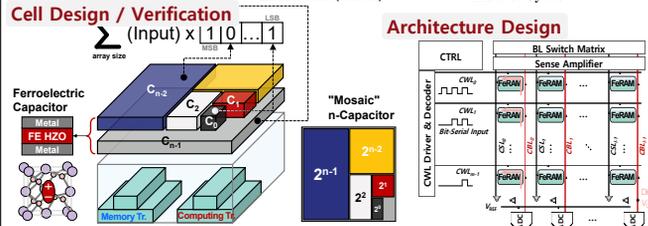
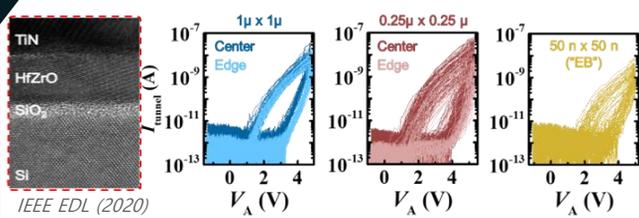
Ferroelectric FET for Flash / Neuromorphic



Ferroelectric RAM for DRAM / CiM



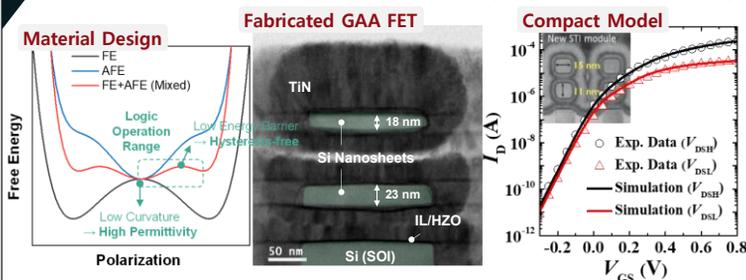
Ferroelectric Tunnel Junction for PUF



Next Generation Logic Devices

MPB Film for Higher-k Logic

Adv. Sci. (2025) IEEE TED (2020)



M3D Ternary SRAM for PIM

